



Characterization of THGEM Detector: A Member of the MPGD Family

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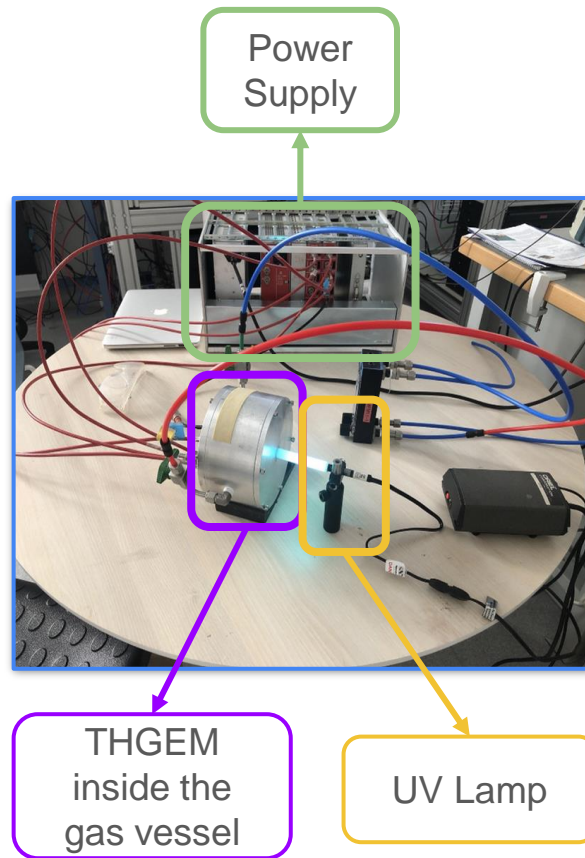
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- Experimental setup
- Gain measurement and results
 - HV scan of the gem field with drift and induction field = 0
 - Gain Scan
 - scan of induction field with fixed gem field and drift field = 0
 - Best collection
 - scan of the drift field with fixed gem field and induction field = 0
 - Best Extraction
 - scan of the gem field with fixed drift (maximum extraction) and induction field (maximum collection at anode)
 - Optimal operation

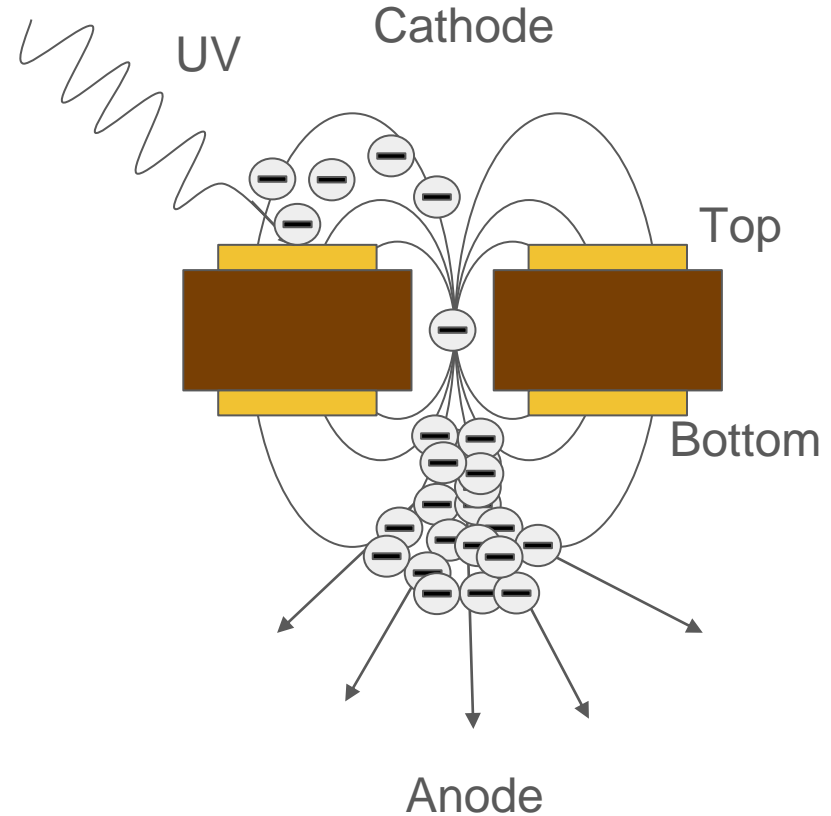
Experimental Setup

- Drift region ~ 5 mm
- Insulator ~ 0.8 mm
 - a. 1 mm pitch hexagonal pattern of 0.5 mm diameter holes (obtained by drilling and etching)
- Induction region ~ 1 mm
- 10 x 10 cm² Thick GEM
- Gas Mixture: Ar/CO₂/iC₄H₁₀ (93:5:2%) flushing
- Sources: UV lamp (Hg) with lines in 200 to 600 nm range
- Keithely 6517A (1pA resolution)
- HV power supply : 4 ch. CAEN HV Module
- A computer for HV control and automated measurements (Labview interface)



Experimental Setup - Photoelectric effect in GEM foils

- Photons from the UV lamp
 - $\lambda \sim 200$ to 600 nm
- Electrons extracted from the copper surface
 - work function ~ 4.5 to 5.1 eV
- The drift lines extracts the electrons and then the multiplication lines drags the electrons into the hole
- The electric currents generated in the cathode, top GEM, bottom GEM and anode are monitored to understand the phenomena

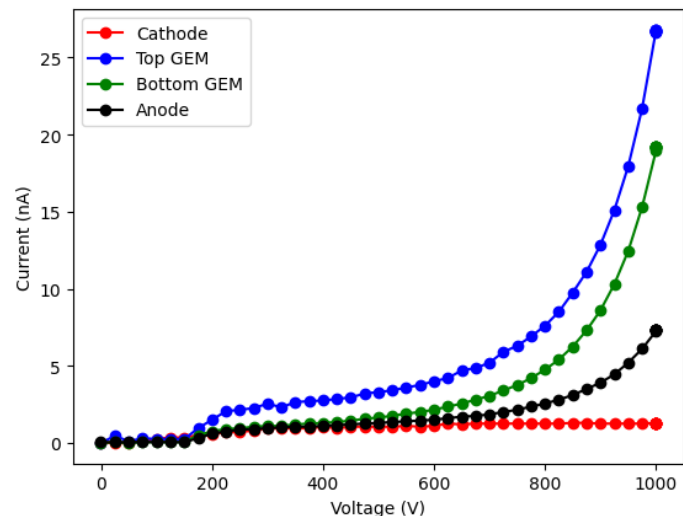
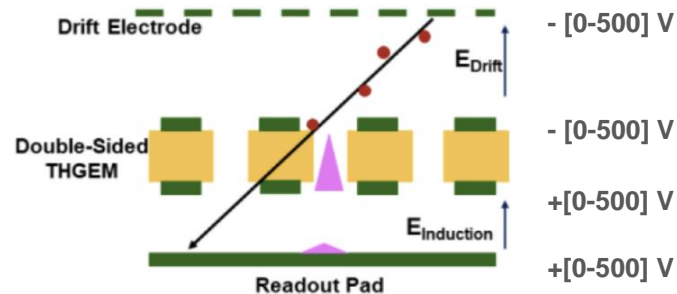


1) HV scan of the gem field

- $\Delta V(\text{drift}) = \Delta V(\text{induction}) = 0\text{V}$
- $V(\text{GEM})$ scanned from 0 to 1000V
→ ΔV GEM scanned from 0V to 1000V
→ opposite polarity tested

ΔV scan from 0 to 500 V → electric field ↓

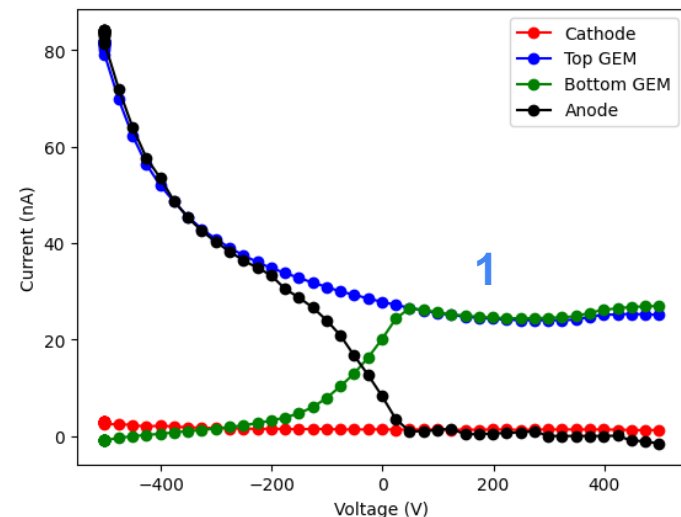
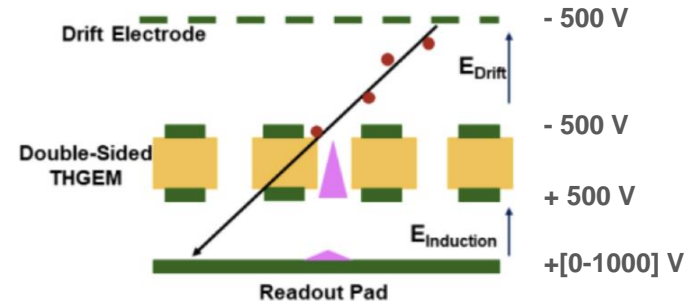
- electrons from the avalanche are pushed towards the bottom electrode of the gem: all the electrons are collected at the bottom electrode of the gem
- most of the ions are collected at the top electrode of the gem
- cathode and anode currents ~ 0



2) Scan of the induction field

- $\Delta V(\text{drift}) = 0\text{V}$, $\Delta V(\text{gem}) = 1000\text{V}$
- $V(\text{anode})$ scanned from 0 to 1000V
→ ΔV anode scanned from -500V to 500V
→ opposite polarity tested

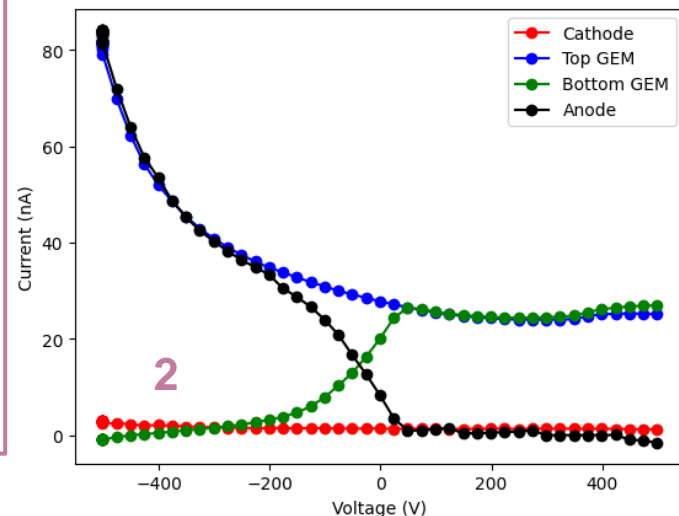
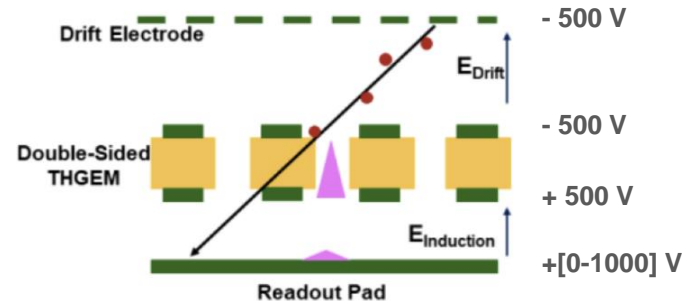
- 1) ΔV scan from 0 to 500 V → electric field ↓
- electrons from the avalanche are pushed towards the bottom electrode of the gem: all the electrons are collected at the bottom electrode of the gem
 - most of the ions are collected at the top electrode of the gem
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2) Scan of the induction field

- $\Delta V(\text{drift}) = 0\text{V}$, $\Delta V(\text{gem}) = 1000\text{V}$
- $V(\text{anode})$ scanned from 0 to 1000V
→ ΔV anode scanned from -500V to 500V
→ opposite polarity tested

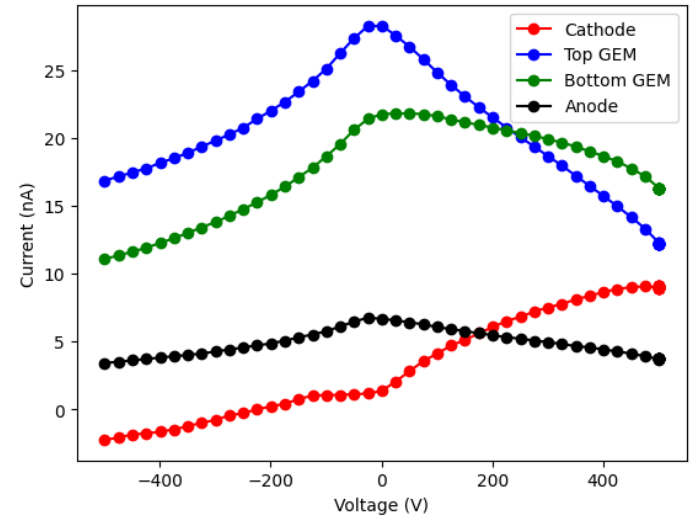
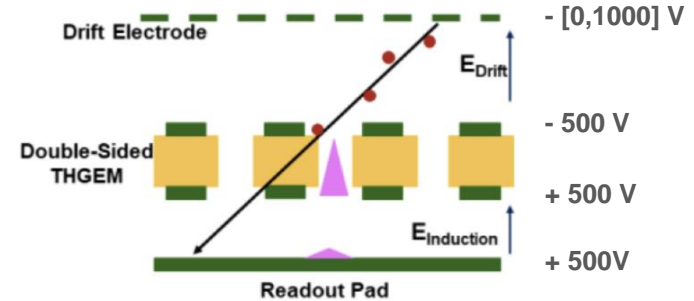
- 2) ΔV scan from 0 to -500 V → electric field ↑
nominal direction of the electric field
- as the electric field increases the electrons from the avalanche are directed towards the anode
→ the anode current increases and the gem bottom current decreases
 - from ~ -200 V all the electrons are collected at the anode
 - from ~ -350 V we start to observe the multiplication process in the induction gap



3) Scan of the drift field

- $\Delta V(\text{induction}) = 0\text{V}$, $\Delta V(\text{gem}) = 1000\text{V}$
- $V(\text{cathode})$ scanned from 0 to -1000V
→ ΔV cathode scanned from -500V to 500V
→ nominal and opposite polarity tested

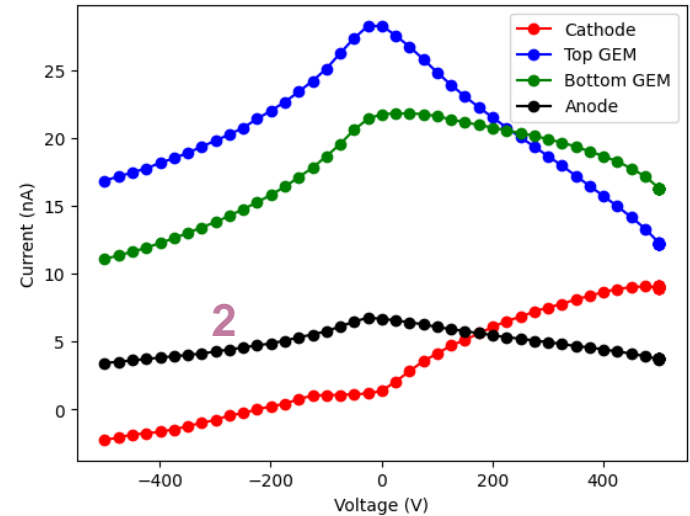
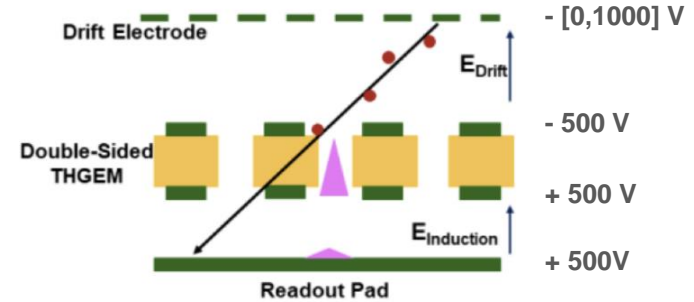
- 1) ΔV scan from 0 to 500 V → electric field ↓
- some of the electrons extracted from the top gem are drifted towards the cathode → the cathode current increases with ΔV
 - less electrons start an avalanche → less ions and secondary electrons produced
→ top and bottom gem currents and anode current decrease with ΔV



3) Scan of the drift field

- $\Delta V(\text{induction}) = 0\text{V}$, $\Delta V(\text{gem}) = 1000\text{V}$
- $V(\text{cathode})$ scanned from 0 to -1000V
 - ΔV cathode scanned from -500V to 500V
 - nominal and opposite polarity tested

- 2) ΔV scan from 0 to -500V → electric field ↑
- the electrons extracted are pushed towards the top gem electrode and some of the ions towards the cathode → small negative cathode current
 - the drift field reduces the number of electrons extracted from the top gem → less electrons start avalanches → top and bottom gem currents and anode current decrease with ΔV

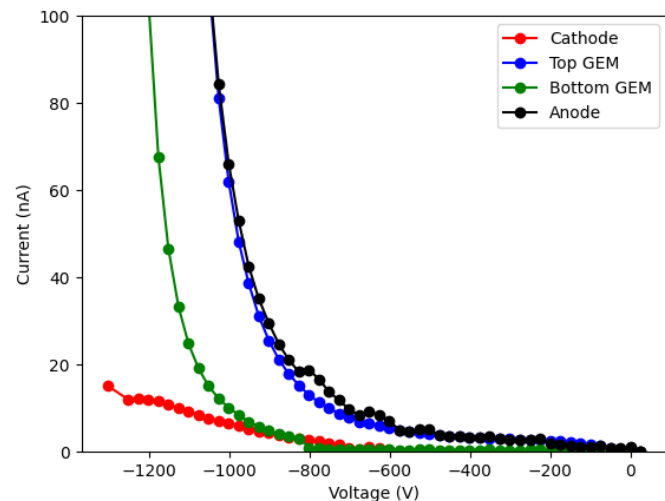
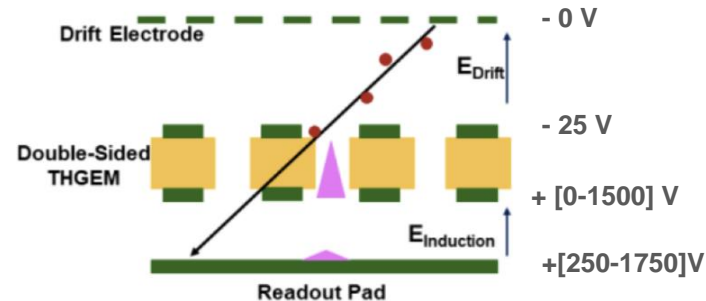


4) Gain in maximum extraction and induction

- $\Delta V(\text{drift}) = -25\text{V}$
- $\Delta V(\text{GEM})$ scanned from 0 to -1500V
- $\Delta V(\text{Induction})$ scanned from
→ ΔV cathode scanned from -500V to 500V
→ nominal and opposite polarity tested

ΔV scan from 0 to $+1500\text{V}$ → gain ↑ (around 10^2)

- the electrons extracted are dragged by the electric field inside the hole where multiplication takes place
- the current in the top gem and the anode are very similar and much higher than the current in the bottom and the cathode
- Could not reach a maximum gain due to overcurrent



Conclusion

- Multiplication:
 - Almost no multiplication in ΔV below - 600V
 - Exponential growth in the gain in ΔV above - 600V
- Inverted Polarity:
 - Reversed induction field: higher current measured in the bottom
 - Matching induction field: higher current measured in the anode
 - top GEM measured the same current as the bottom/anode
- Voltage setup:
 - application of a GEM-based detector for photoelectric effect
 - optimal operation: best extraction and best collection of the electrons
 - Could reach higher gains